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INFORMATION DISCLOSURE STATEMENT BY APPLICANT

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Sheet 1 of 1

Complete if Known	
Application Number	10/535,358
Filing Date	
First Named Inventor	Andrew R. Barron
Group Art Unit	
Examiner Name	
Attorney Docket Number	1789-09405 (21050) CWS

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Examiner Initials*	Cite No.[1]	Document Number Number-Kind Code[2] (*if known*)	Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
/TD/	AA	US-6,080,683	06/27/2000	Fauv et al.	
	AB	US-5,073,408	12/17/1991	Goda et al.	
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OTHER PRIOR ART -- NON PATENT LITERATURE DOCUMENTS

Examiner Initials*	Cite No.[1]	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate) title of the item (book, magazine, journal, serial, symposium, catalog, etc), date, page(s), volume-issued number(s), publisher, city and/or country where published.	T[2]
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Examiner Signature	/Trung Dang/	Dated Considered	08/05/2008